

 FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.106C1	APPLICATION NO. 10/027,519
	APPLICANT Li et al.	
	FILING DATE December 20, 2001	GROUP Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
VU	5,807,607	9/15/98	Smith et al.			
VY	5,843,535	12/1/98	Dobson			
VY	5,874,367	2/23/99	Dobson			
VY	5,858,880	1/12/99	Dobson et al.			
VY	5,972,862	10/26/99	Torii et al.			
VY	6,008,540	12/28/99	Lu et al.			
VY	6,076,585	6/20/00	Klingbeil et al.			
VY	6,130,152	10/10/00	Smith et al.			
VY	6,140,245	10/31/00	Sharan			

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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
VY	Advanced SiO ₂ Planarization Using Silane and H ₂ O ₂ , Semiconductor International 86, December 1994, pp. 86-88.
VY	Techniques for Planarizing Device Topography, Kathy Skidmore, April 1988, pp. 115-119.
VY	Allied Signal Advanced Materials, Spin/Bake/Cure Procedure for Spin-On-Glass Materials for Interlevel and Internetal Dielectric Planarization, pp. 1-5.
VY	TechNotes, Advanced Electronics Resins, Dow Chemical Company, Process Guide for Photo-Imageable BCB, pp. 1-5.

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EXAMINER <i>J. Theis</i>	DATE CONSIDERED <i>11/07/03</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	